

CND0214A

Infrared Optocal Module (IrDA)

Infrared data link for cellular phones, peripheral devices

■ Features

- Compliant with IrDA Ver.1.2
- Corresponding low I/O (interface) voltage: 1.5 V
- Corresponding reflow solder (260°C)
- Ultra-small top view package (2.0 mm × 8.2 mm × 1.7 mm)

■ Type

- GaAlAs LED + IC + PIN Photodiode

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Operating supply voltage	V_{CC}	-0.5 to +3.8	V
Output voltage	V_O	-0.5 to +3.8	V
Input voltage	V_I	-0.5 to +3.8	V
Shutdown input voltage	V_{SD}	-0.5 to +3.8	V
LED operating supply voltage	V_{LEDA}	-0.5 to +7.0	V
Pulse forward current *	I_{FP}	200	mA
Low level output current	I_{OL}	10	mA
Operating ambient temperature	T_{opr}	-20 to +70	°C
Storage temperature	T_{stg}	-30 to +85	°C

Note) *: $t_w \leq 90 \mu\text{s}$, Duty $\leq 20\%$

■ Operating Condition

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Operating supply voltage	V_{CC}		2.4	2.8	3.3	V
LED operating supply voltage	V_{LEDA}		2.7		4.5	V
Input / output supply voltage	V_{IO}		1.5	1.8	V_{CC}	V

■ Electrical-Optical Characteristics $V_{CC} = V_{IO} = 2.8 \text{ V}$, $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
High level supply current *1	I_{CCH}	$V_{LED} = 3.6 \text{ V}$, $V_I = 0.5 \text{ V}$, $V_{SD} \leq 0.5 \text{ V}$		90	120	μA
Shut down supply current *1	I_{CCSD}	$V_I = 0.5 \text{ V}$, $V_{IO} \geq V_{SD} \geq V_{IO} - 0.3$ (SD = High)		10	200	nA
Maximum reception distance *5	L_{max}	$V_{LED} = 2.7 \text{ V}$ to 4.5 V , $V_{SD} \leq 0.5 \text{ V}$, External components	23			cm
Data Rates	—		9.6		115.2	kbps
SD high level input voltage	V_{IHSD}		$V_{IO} - 0.5$		V_{IO}	V
SD low level input voltage	V_{ILSD}		0		0.5	V

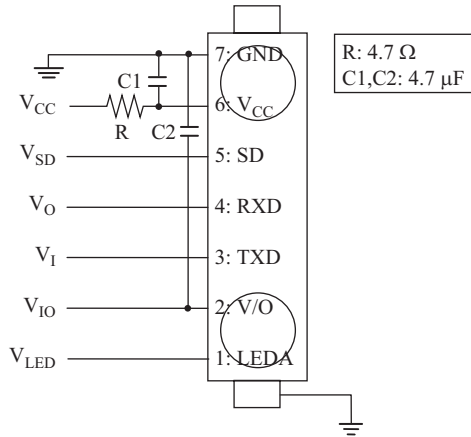
■ Electrical-Optical Characteristics (Continued) $V_{CC} = V_{IO} = 2.8 \text{ V}$, $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Transmitter						
Peak emission wavelength	λ_p	$I_{FP} = 60 \text{ mA}$, Duty 3/16	850	870	900	nm
Pulse forward current ^{*1}	I_{FP}	$V_{LED} = 3.2 \text{ V}$, $V_{SD} \leq 0.5 \text{ V}$	40	60	90	mA
Center radiant intensity ^{*1,2}	$\theta_T = 0$	I_e , $V_{LED} = 3.2 \text{ V}$, $V_{SD} \leq 0.5 \text{ V}$	12	18		mW/sr
	$\theta_T = \pm 15$	I_{e15} , $V_{LED} = 3.2 \text{ V}$, $V_{SD} \leq 0.5 \text{ V}$	7	12		mW/sr
High level input voltage ^{*1}	V_{IH}	$V_{CC} = 2.4 \text{ V to } 3.3 \text{ V}$, $V_{SD} \leq 0.5 \text{ V}$	$V_{IO} - 0.5$		V_{IO}	V
Low level input voltage ^{*1}	V_{IL}	$V_{CC} = 2.4 \text{ V to } 3.3 \text{ V}$, $V_{SD} \leq 0.5 \text{ V}$	0		0.5	V
TX half-angle	θ_T		± 15			°
LED optical pulse width	T_{WT}	TXD Pulse = 1.6 μs	1.41	1.6	2.2	μs
Rise time ^{*1,3}	t_r	$t_w = 1.6 \mu\text{s}$, $R_L = 50 \Omega$			0.2	μs
Fall time ^{*1,3}	t_f	$t_w = 1.6 \mu\text{s}$, $R_L = 50 \Omega$			0.2	μs
TX wake up time ^{*8}	t_{Twu}			0.3	1	μs
Receiver						
Minimum input irradiance	$E_{I \min}$	$V_{SD} \leq 0.5 \text{ V}$			5	$\mu\text{W/cm}^2$
High level output voltage ^{*6}	V_{OH}	Non signal condition $I_{OH} = -200 \mu\text{A}$, $V_{SD} \leq 0.5 \text{ V}$	$V_{IO} - 0.3$		V_{IO}	V
Low level output voltage ^{*7}	V_{OL}	$I_{OL} = 500 \mu\text{A}$, $V_{SD} \leq 0.5 \text{ V}$	0		0.5	V
RX half angle	θ_R		± 15			°
RXD output pulse width	T_{WR}	$C_L = 15 \text{ pF}$, 9.6 kbps to 115.2 kbps	1.0	2.3	4.2	μs
RX wake up time ^{*9}	t_{Rwu}	$E_I = 8.1 \mu\text{W/cm}^2$		200	400	μs
Receiver latency time	t_L	$E_I = 8.1 \mu\text{W/cm}^2$		100	200	μs
Rise time ^{*4}	t_r	$C_L = 10 \text{ pF}$		50	200	ns
Fall time ^{*4}	t_f	$C_L = 10 \text{ pF}$		50	200	ns

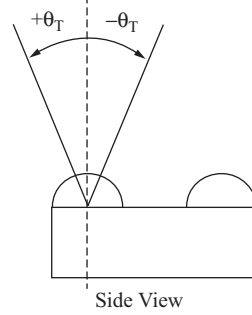
■ Electrical-Optical Characteristics (Continued)

Note) Measuring circuit

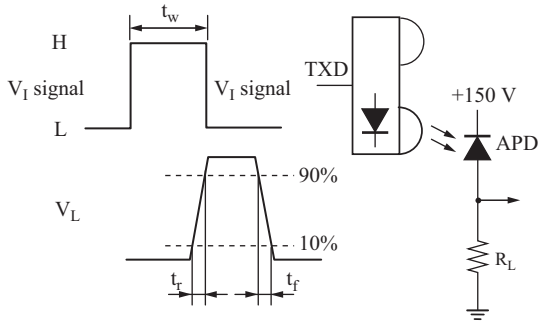
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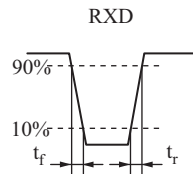
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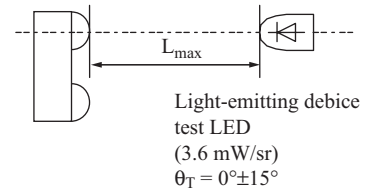
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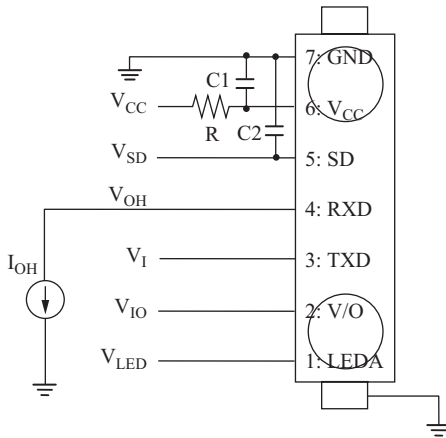
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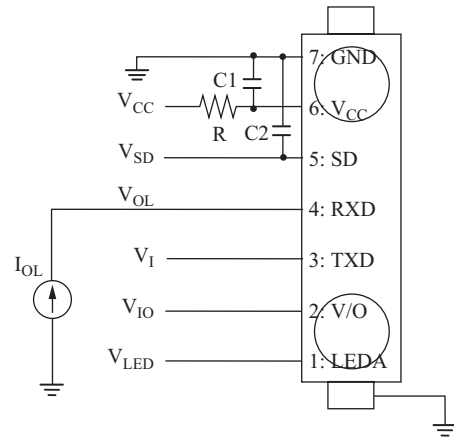
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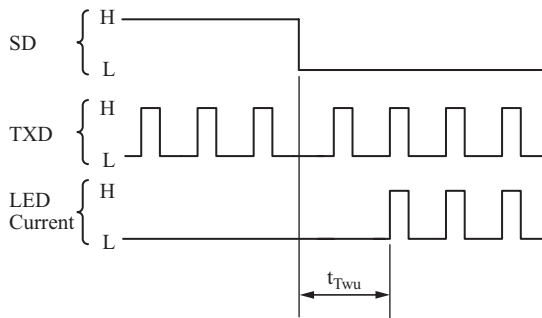


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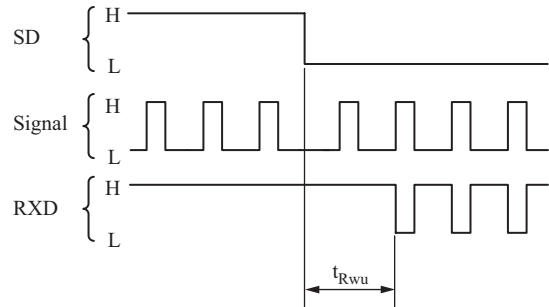
*8:

TX wake up time

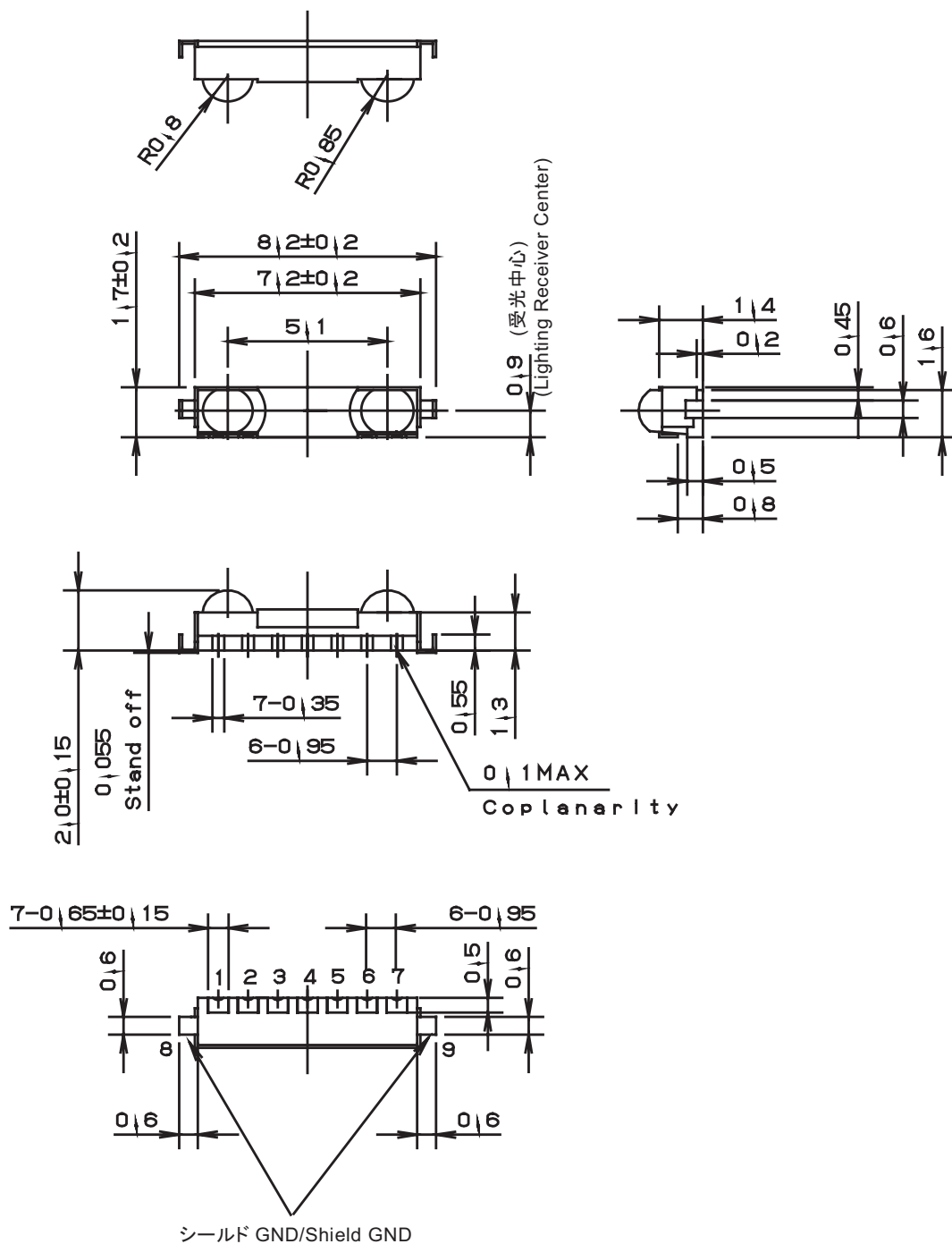


*9:

RX wake up time



■ Package (Unit: mm)



• Pin name

- | | |
|-------------|---------------|
| 1. LEDA | 6. V_{CC} |
| 2. V_{IO} | 7. GND |
| 3. TXD | 8. Shield GND |
| 4. RXD | 9. Shield GND |
| 5. SD | |

Caution for Safety

 **DANGER**

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.

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